## IN THE CLAIMS

Please carcel claims 1-4 without prejudice or disclaimer of the subject matter contained therein.

Please amend the claims as follows:

5. (Twice Amended) A method for manufacturing a semiconductor device comprising:

preparing a semiconductor substrate of a first conductivity type;

forming scribe lanes in the semiconductor substrate, said scribe lanes defining chip formation areas and containing only an unetched portion of the semiconductor substrate;

forming a deep well area in each chip formation area, each deep well area having a second conductivity type opposite the first conductivity type; and forming at least one well area within the deep well area.

8. (Three Times Amended) A method for manufacturing semiconductor device comprising:

preparing a semiconductor substrate of a first conductivity type;

forming scribe lanes in the semiconductor substrate, said scribe lanes defining chip formation areas;

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10 CJ forming a deep well area in each chip formation area, each deep well area having a second conductivity type opposite the first conductivity type; and forming at least one well area within the deep well area,

wherein the first conductivity type is a n-type conductor; and the second conductivity type is a p-type conductor.



10. (Three Times Amended) A method for manufacturing a semiconductor device comprising:

preparing a semiconductor substrate of a first conductivity type;

forming scribe lanes in the semiconductor substrate, said scribe lanes defining chip formation areas and containing only an unetched portion of the semiconductor surface;

forming a deep well area in each chip formation area, each deep well area having a second conductivity type opposite the first conductivity type; and

wherein a first conductive well area and a second conductive well area are separately formed within the deep well area,

the first conductive well area is formed of the first conductivity type, and the second conductive well area is formed of the second conductivity type.